

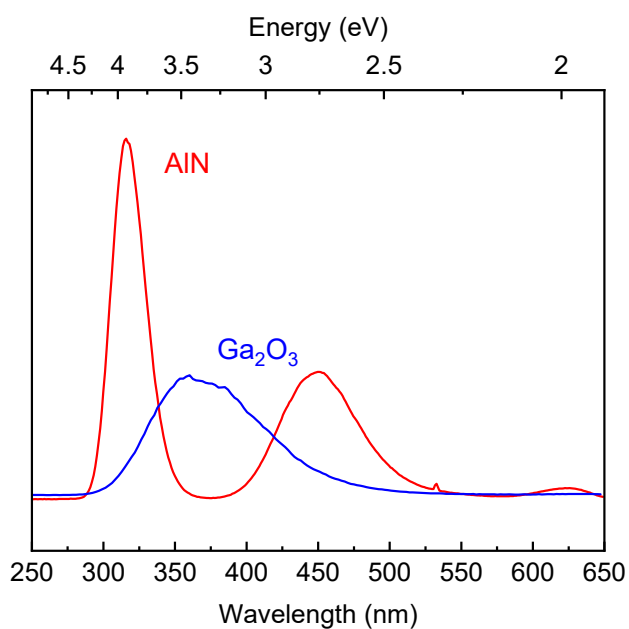
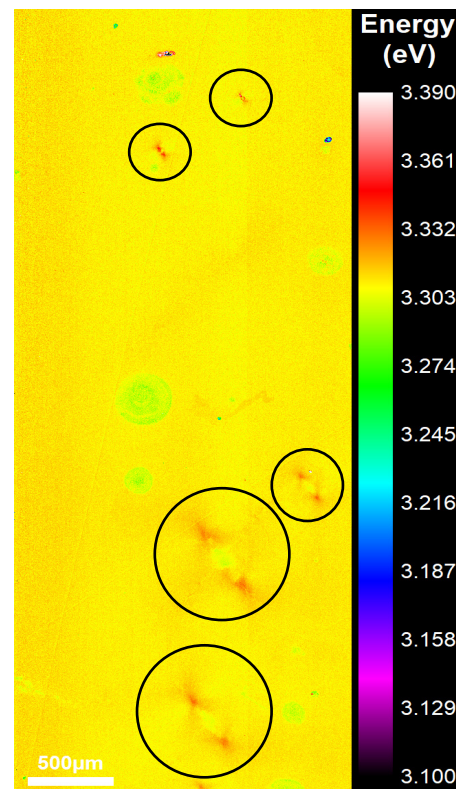
Deep-UV photoluminescence (PL) spectroscopy



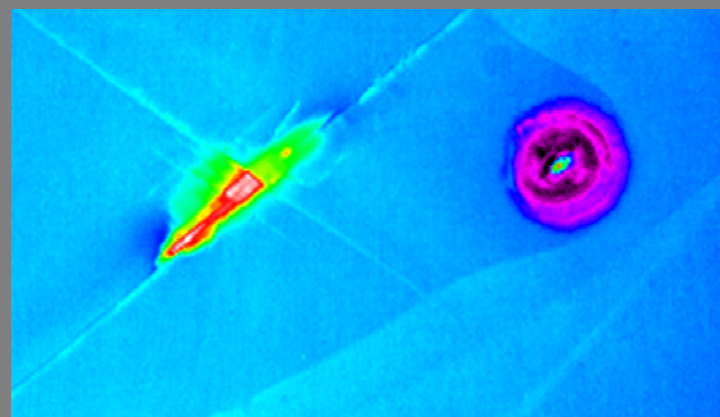
The Mini Pro with the deep-UV kit provides PL spectroscopy at **266 nm excitation**, enabling studies of ultra-wide bandgap semiconductors such as Ga_2O_3 and AlN .



Mapping the position of the PL band (eV) of $\beta\text{-Ga}_2\text{O}_3$ enables sensitive detection of **defects** such as dislocations.



PL spectra of AlN and $\beta\text{-Ga}_2\text{O}_3$ crystals.



PL intensity map of $\beta\text{-Ga}_2\text{O}_3$ epilayer, showing a crack (left) and conchoidal fracture (right, diameter ~ 0.3 mm).